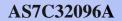


专业PCB打样工厂,24小时加急出货 捷多邦

February 2005 **Preliminary Information**



SC.COM

NC NC

NC

A17

A16

A15

A14

OE

I/08

I/O7

GND

CC

I/06

I/O5

A13

A12

A11

A10

NC NC

44

43

42

41 40

39

38 37 36

26 25

3.3V 256K × 8 CMOS SRAM

R

Features

- Industrial and commercial temperature
- Organization: 262,144 words × 8 bits
- Center power and ground pins
- High speed

odt.d

.con

2/24/05, v. 1.0

- 10/12/15/20 ns address access time
- 4/5/6/7 ns output enable access time
- Low power consumption: ACTIVE
- 650 mW / max @ 10 ns
- Low power consumption: STANDBY
- 28.8 mW / max CMOS

- Equal access and cycle times
- Easy memory expansion with \overline{CE} , \overline{OE} inputs
- TTL-compatible, three-state I/O
- JEDEC standard packages - 44-pin TSOP 2
- ESD protection \geq 2000 volts
- Latch-up current $\geq 200 \text{ mA}$

Logic block diagram **Pin arrangements** 44-pin TSOP 2 NC V_{CC} $1 \circ$ NC 23456789 GND-A0 Input buffer A1 A2 A0 A1 A3 I/O1 A4 CE Row decoder A2 Sense amp $262,144 \times 8$ A3 I/O1 Α4 Array A5 I/O2 10 (2,097,152)A6 11 A7 CC I/08 12 GND A8 13 14 A9 I/O3 Δ <u>I/O4</u> Column decoder WF WE 15 Control 16 17 Circuit A5 A6 18 A7 19 A8 A9 20

Selection guide	市场网		NC NC		24 NC 23 NC	
	750.00	-10	-12	-15	-20	Unit
Maximum address access time		10	12	15	20	ns
Maximum output enable access time		4	5	6	7	ns
Maximum operating current	Industrial	180	160	140	110	mA
	Commercial	170	150	130	100	mA
Maximum CMOS standby current		8	8	8	8	mA

Alliance Semiconductor

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AS7C32096A



Functional description

The AS7C32096A is a high-performance CMOS 2,097,152-bit Static Random Access Memory (SRAM) device organized as 262,144 words $\times 8$ bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times (t_{AA} , t_{RC} , t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 4/5/6/7 ns are ideal for high-performance applications. The chip enable input \overline{CE} permits easy memory expansion with multiple-bank memory systems.

When $\overline{\text{CE}}$ is high the device enters standby mode. The device is guaranteed not to exceed 28.8mW power consumption in CMOS standby mode.

A write cycle is accomplished by asserting write enable (\overline{WE}) and chip enable (\overline{CE}). Data on the input pins I/O1–I/O8 is written on the rising edge of \overline{WE} (write cycle 1) or \overline{CE} (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (\overline{OE}) or write enable (\overline{WE}).

A read cycle is accomplished by asserting output enable (\overline{OE}) and chip enable (\overline{CE}), with write enable (\overline{WE}) high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible, and operation is from a single 3.3V supply voltage. This device is available as per industry standard 44-pin TSOP 2 package.

Parameter Min **Symbol** Max Unit Voltage on V_{CC} relative to GND V V_{t1} -0.5 +5.0V Voltage on any pin relative to GND V_{t2} -0.5V_{CC} +0.5 Power dissipation 1.0 W PD _ °C Storage temperature (plastic) T_{stg} -65+150Temperature with V_{CC} applied -55 +125°C T_{bias} 20 DC current into output (low) mA I_{OUT} _

Absolute maximum ratings

NOTE: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

CE	WE	OE	Data	Mode
H	X	Х	High Z	Standby (I _{SB} , I _{SB1})
L	Н	Н	High Z	Output disable (I _{CC})
L	Н	L	D _{OUT}	Read (I _{CC})
L	L	Х	D _{IN}	Write (I _{CC})

Key: X = Don't care, L = Low, H = High



Recommended operating condition

Param	eter	Symbol	Min	Nominal	Max	Unit
Supply voltage		V _{CC} (10/12/15/20)	3.0	3.3	3.6	V
Input voltage		V _{IH} **	2.0	_	V _{CC} + 0.5	V
input voltage		V _{IL} *	-0.5	_	0.8	V
Ambient operating	commercial	T _A	0	-	70	°C
temperature industrial		T _A	-40	-	85	°C

 $V_{IL} \min = -1.0V$ for pulse width less than 5ns. $V_{IH} \max = V_{CC} + 2.0V$ for pulse width less than 5ns.

DC operating characteristics (over the operating range) I

				-	10	_]	12	-1	15	-2	20	
Parameter	Symbol	Test conditions		Min	Max	Min	Max	Min	Max	Min	Max	Unit
Input leakage current	I _{LI}	$V_{CC} = Max, V_{IN} = GND$	to V _{CC}	_	1	N.	1		1	_	1	μΑ
Output leakage current	I _{LO}	$V_{CC} = Max, \overline{CE} = V$ $V_{OUT} = GND \text{ to } V_{CC}$		I	1	I	1	Ι	1	_	1	μΑ
Operating power	I _{CC}	$V_{CC} = Max, \overline{CE} \le V_{IL}$	Industrial		180	_	160	_	140	_	110	mA
supply current	1CC		Commercial	-	170	-	150	-	130	-	100	mA
	I _{SB}	$V_{CC} = Max, \overline{CE} \ge V_{IH}, f$	= f _{Max}	-	60	-	60	-	60	-	60	mA
Standby power supply current	I _{SB1}	$V_{CC} = Max,$ $\overline{CE} \ge V_{CC} - 0.2V,$ $V_{IN} \le 0.2V \text{ or } V_{IN} \ge V_{CC}$ f = 0	– 0.2V,	1	8		8	-	8		8	mA
Output voltage	V _{OL}	$I_{OL} = 8 \text{ mA}, V_{CC} = N$	lin	I	0.4	I	0.4	Ι	0.4	-	0.4	V
Sulput Voltage	V _{OH}	$I_{OH} = -4 \text{ mA}, V_{CC} = N$	Min	2.4	-	2.4	-	2.4	-	2.4	-	V

Capacitance (f = 1MHz, $T_a = 25^\circ \text{ C}$, $V_{CC} = \text{NOMINAL})^4$

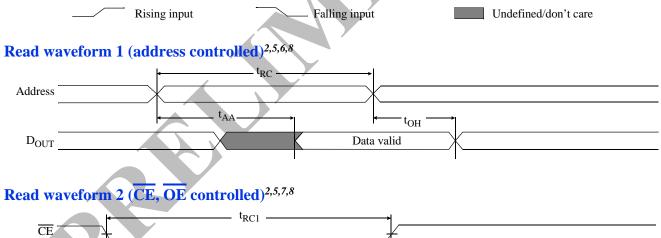
Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C _{IN}	A, \overline{CE} , \overline{WE} , \overline{OE}	$V_{IN} = 0V$	5	pF
I/O capacitance	C _{I/O}	I/O	$V_{IN} = V_{OUT} = 0V$	7	pF

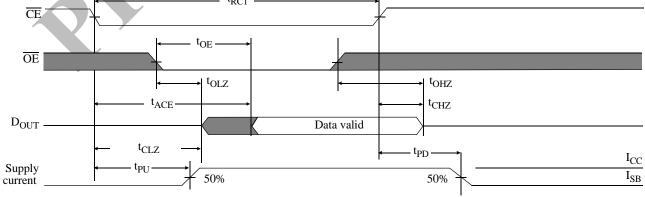
AS7C32096A

Read cycle (over the operating range)^{2,8}

		_]	10	-1	12	-1	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t _{RC}	10	Ι	12	-	15	-	20	-	ns	
Address access time	t _{AA}	_	10	_	12	-	15	-	20	ns	2
Chip enable (\overline{CE}) access time	t _{ACE}	_	10	_	12	-	15	-	20	ns	2
Output enable (\overline{OE}) access time	t _{OE}	_	4	_	5	-	6	~-	7	ns	
Output hold from address change	t _{OH}	3	_	3	_	3	-	3	-	ns	4
$\overline{\text{CE}}$ Low to output in low Z	t _{CLZ}	3	_	3	_	3	-	3	/ _	ns	3,4
$\overline{\text{CE}}$ High to output in high Z	t _{CHZ}	_	5	_	6	-	7		9	ns	3,4
OE Low to output in low Z	t _{OLZ}	0	_	0	_	0	-	0	-	ns	3,4
$\overline{\text{OE}}$ High to output in high Z	t _{OHZ}	_	5	_	6	F	7	_	9	ns	3,4
Power up time	t _{PU}	0	-	0	-	0	_	0	-	ns	3,4
Power down time	t _{PD}	_	10		12		15	_	20	ns	3,4

Key to switching waveforms



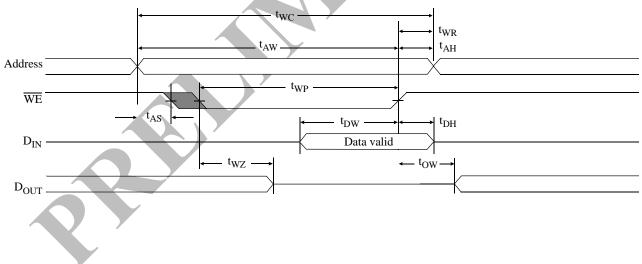




Write cycle (over the operating range)⁹

		-1	10	_]	12	-1	15	—í	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write cycle time	t _{WC}	10	-	12	-	15	_	20	-	ns	
Chip enable (\overline{CE}) to write end	t _{CW}	7	_	8	_	10	_	12	_	ns	
Address setup to write end	t _{AW}	7	-	8	-	10	_	12	-	ns	
Address setup time	t _{AS}	0	-	0	-	0	-	0	-	ns	
Write pulse width ($\overline{OE} = high$)	t _{WP1}	7	-	8	_	10	-	12	-	ns	
Write pulse width ($\overline{OE} = low$	t _{WP2}	10	-	12	_	15	-	20	-	ns	
Address hold from end of write	t _{AH}	0	_	0	_	0		0	_	ns	
Write recovery time	t _{WR}	0	_	0	-	0	-	0	-	ns	
Data valid to write end	t _{DW}	5	-	6	_	7		9	-	ns	
Data hold time	t _{DH}	0	-	0		0	<i>_</i>	0	-	ns	3,4
Write enable to output in high Z	t _{WZ}	0	5	0	6	0	7	0	9	ns	3,4
Output active from write end	t _{OW}	3	-	3	-	3	_	3	_	ns	3,4

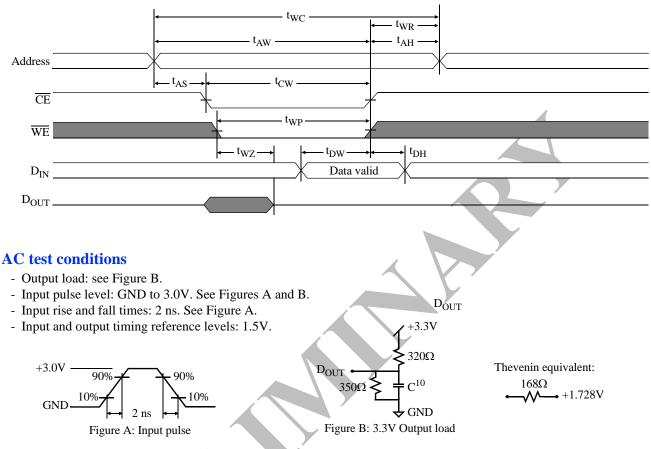
Write waveform 1 ($\overline{\text{WE}}$ controlled)⁹



AS7C32096A



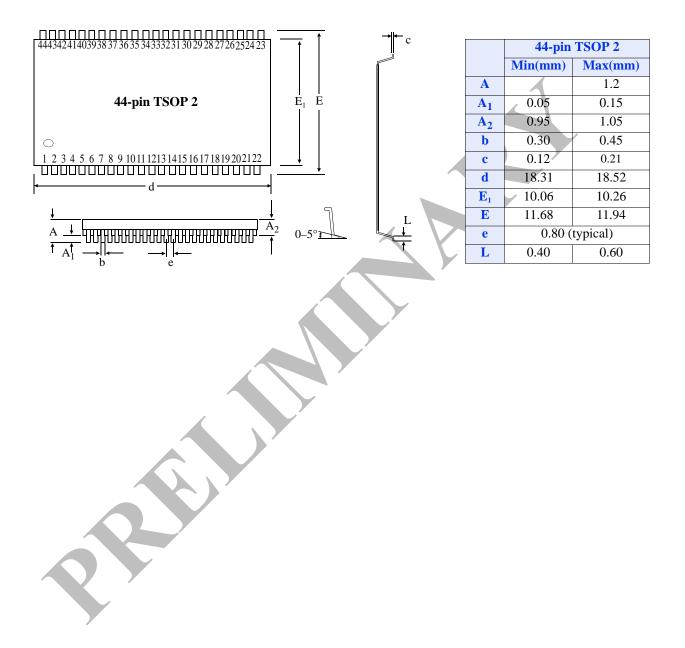
Write waveform 2 (CE controlled)⁹



Notes

- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.
- 2 For test conditions, see AC Test Conditions.
- 3 t_{CLZ} and t_{CHZ} are specified with $C_L = 5pF$ as in Figure B. Transition is measured $\pm 500 \text{ mV}$ from steady-state voltage.
- 4 This parameter is guaranteed, but not tested.
- 5 $\overline{\text{WE}}$ is HIGH for read cycle.
- 6 $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are LOW for read cycle.
- 7 Address valid prior to or coincident with $\overline{\text{CE}}$ transition Low.
- 8 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 9 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 10 C=30pF, except on High Z and Low Z parameters, where C=5pF.

Package dimensions





Ordering codes

Package	Temperature	10 ns	12 ns	15 ns	20 ns
TSOP 2	Commercial	AS7C32096A-10TC	AS7C32096A-12TC	AS7C32096A-15TC	AS7C32096A-20TC
1501 2	Industrial	AS7C32096A-10TI	AS7C32096A-12TI	AS7C32096A-15TI	AS7C32096A-20TI

Note: Add suffix 'N' to the above part number for Lead Free Parts. (Ex: AS7C32096A - 10TIN)

Part numbering system

AS7C	X	2096A	-XX	Т	X	X
SRAM prefix	Voltage: 3 - 3.3V CMOS	Device number	Access time	TO TSOP 2	Temperature ranges: C: Commercial, 0°C to 70°C I: Industrial, –40°C to 85°C	





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